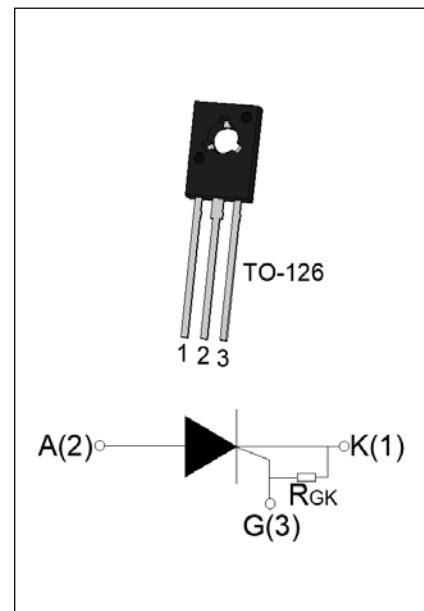




The JR0405Q SCR with the parallel resistor between Gate and Cathode, $R_{GK}=10\sim80k$, is especially recommended for use on straight hair, igniter, anion generator, etc. Package TO-126 is RoHS compliant.

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM}/V_{RRM}	600	V
I_{GT}	200	μA



Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125 ^①	°C
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	600	V
Average on-state current ($T_c \leq 85^\circ C$)	$I_{T(AV)}$	2.5	A
RMS on-state current ($T_c \leq 85^\circ C$)	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^\circ C$)	I_{TSM}	40	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^\circ C$)		44	
I^2t value for fusing ($t_p=10ms, T_j=25^\circ C$)	I^2t	8	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}, f=100Hz, T_j=125^\circ C$)	di/dt	50	$A/\mu s$
Peak gate current ($t_p=20\mu s, T_j=125^\circ C$)	I_{GM}	2	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	0.5	W

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Peak gate power	P_{GM}	5	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

NOTE 1: When we parallel connect a resistor between the drain and source terminals, the T_j can reach $125^\circ C$; if without this resistor, the T_j only can reach $110^\circ C$.

($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L=33$	-	50	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ C$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	6	mA
I_H	$I_T=0.1A$	-	-	5	mA
dV/dt	$V_D=400V T_j=125^\circ C R_{GK}=1K$	50	-	-	V/ μs
	$V_D=400V T_j=125^\circ C R_{GK}=220$	250	-	-	
t_{on}	$I_G=10mA I_A=20mA I_R=2mA$ $T_j=25^\circ C$	-	2	-	μs
t_{off}		-	50	-	

Symbol	Parameter	Value(MAX.)	Unit
V_{TM}	$I_{TM}=8A t_p=380\mu s$	$T_j=25^\circ C$	1.6
V_{TO}	Threshold voltage	$T_j=125^\circ C$	0.64
R_D	Dynamic resistance	$T_j=125^\circ C$	0.08
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ C$	5
I_{RRM}		$T_j=125^\circ C$	0.5

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	7.5	$^\circ C/W T -c$

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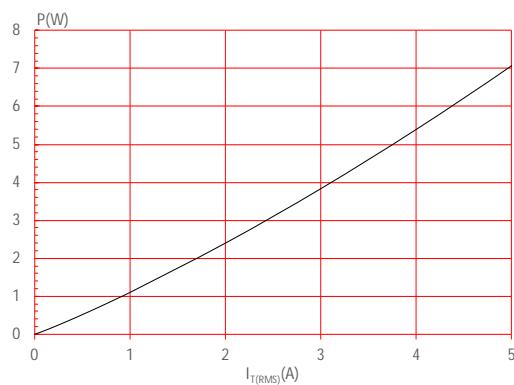
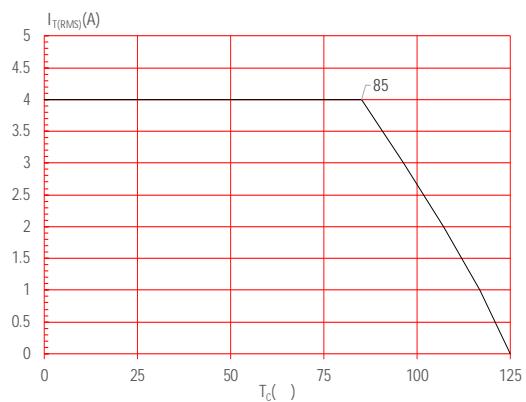
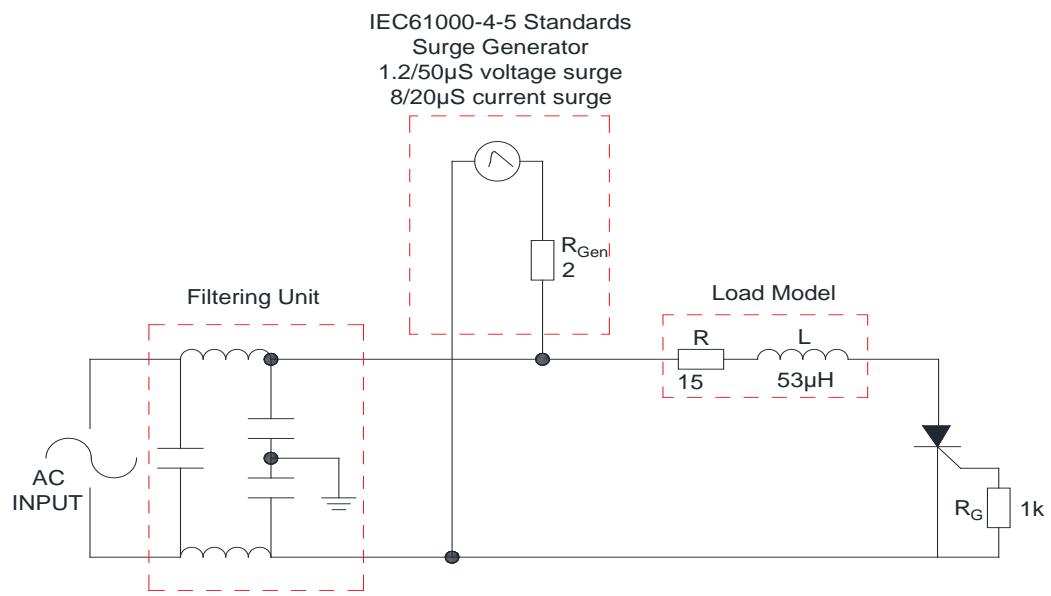
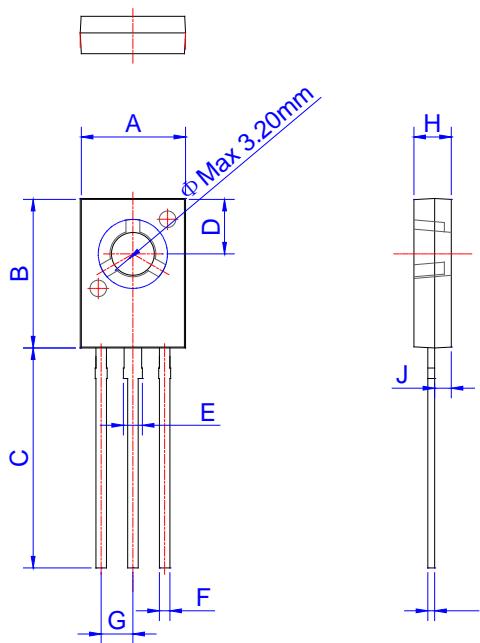
FIG.1 Maximum power dissipation versus RMS on-state current**FIG.3:** Surge peak on-state current versus number of cycles**FIG.2:** RMS on-state current versus case temperature**FIG.4:** On-state characteristics

FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Order code	Voltage $V_{D_{RM}}/V_{R_{RM}}$ (V)	IGT)	Package	Base qty. (pcs)	Delivery mode
			TO-126	500	Bulk Pack



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	7.40		7.80	0.291		0.307
B	10.6		11.2	0.417		0.441
C	15.3		16.3	0.602		0.642
D	3.90		4.10	0.154		0.161
E	1.17		1.47	0.046		0.058
F	0.66		0.86	0.026		0.034
G	2.15		2.45	0.085		0.096
H	2.50		2.90	0.098		0.114
J	1.10		1.50	0.043		0.059
K	0.45		0.60	0.018		0.024

PACKAGE	OUTLINE	BAG (PCS)	INNER BOX (PCS)	CARTON BOX (PCS)
TO-126	Bulk Pack	500	2,000	10,000

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